

60V N-Channel MOSFET



TO-92



Pin Definition:

- 1. Source
- 2. Gate
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (mA)	
60	5 @ V _{GS} = 10V	75	

Features

- Fast Switching Speed
- Low Input and Output Leakage

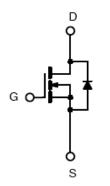
Application

- Direct Logic-Level Interface: TTL/CMOS
- Solid-State Relays

Ordering Information

Part No.	Package	Packing
TSM2N7000CT B0	TO-92	1Kpcs / Bulk
TSM2N7000CT A3	TO-92	2Kpcs / Ammo

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	ter		Limit	Unit	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	200	mA	
Pulsed Drain Current		I _{DM} 500		mA	
Continuous Source Current (Diode Cond	luction) ^{a,b}	I _S	500	mA	
	Ta = 25°C	D	350	\A/	
Maximum Power Dissipation		280	mW		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	10	S
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	357	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



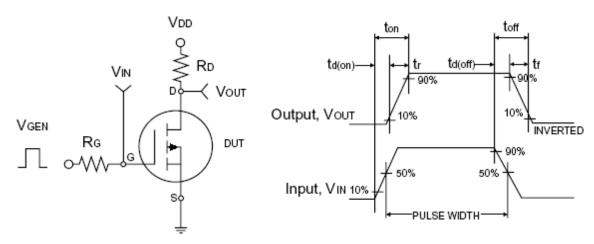
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Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1mA$	$V_{GS(TH)}$	8.0		3.0	V
Gate Body Leakage	$V_{GS} = \pm 15V, V_{DS} = 0V$	I _{GSS}			±10	nA
Zero Gate Voltage Drain Current	$V_{DS} = 48V, V_{GS} = 0V$	I _{DSS}			1.0	μA
Dunin Course On State Besistance	$V_{GS} = 10V, I_D = 75mA$	0			5.3	Ω
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 75mA$	$R_{DS(ON)}$			5	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	g _{fs}	100			mS
Diode Forward Voltage	I _S = 200mA, V _{GS} = 0V	V_{SD}		1.3	1.5	V
Dynamic ^b						
Input Capacitance	\/ - 05\/ \/ - 0\/	C _{iss}		60		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		25		pF
Reverse Transfer Capacitance	7 I - 1.0IVIDZ	C _{rss}		5		
Switching ^c						
Turn-On Rise Time	$V_{DD} = 15V, R_L = 30\Omega,$ $I_D = 200mA,$	t _r		10		200
Turn-Off Fall Time	$V_{GEN} = 10V, R_G = 25\Omega$	t _f		10		nS

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

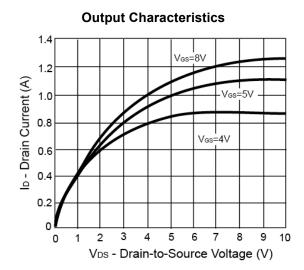
Switchin Waveforms



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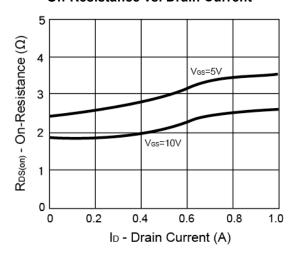


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

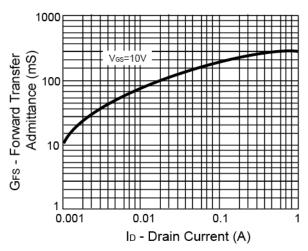


Transfer Characteristics 1.4 1.2 Ib - Drain Current (A) 1.0 0.8 0.6 0.4 0.2 5 9 4 6 10 0 V_{GS} - Gate-to-Source Voltage (V)

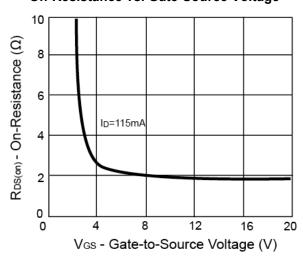
On-Resistance vs. Drain Current



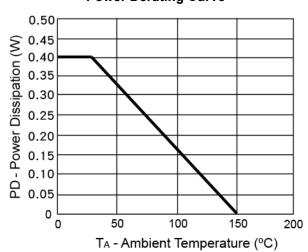
Forward Transfer Admittance vs. Drain Current



On-Resistance vs. Gate-Source Voltage



Power Derating Curve

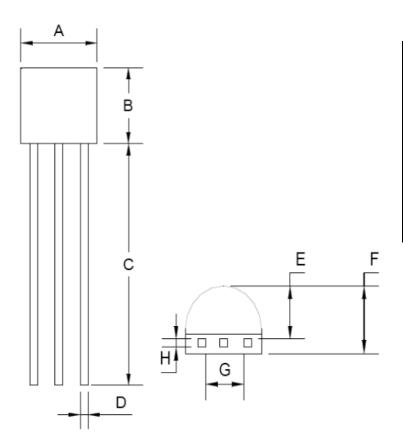




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TO-92 Mechanical Drawing



TO-92 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	4.30	4.70	0.169	0.185	
В	4.30	4.70	0.169	0.185	
С	14.30(typ)		0.563(typ)		
D	0.43	0.49	0.017	0.019	
Е	2.19	2.81	0.086	0.111	
F	3.30	3.70	0.130	0.146	
G	2.42	2.66	0.095	0.105	
Н	0.37	0.43	0.015	0.017	



TSM2N7000 60V N-Channel MOSFET

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